

Trench MOS Barrier Schottky Rectifier

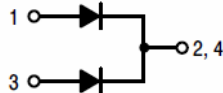
TO-220AB
TSR20L200CT



ITO-220AB
TSR20L200CTF



TO-263
TSR20L80CTB



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			VRRM	200		V
Maximum average forward rectified current	per device		IF(AV)	20		A
	per diode			10		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			IFSM	180		A
Operating junction and storage temperature range			TJ, TSTG	-65 to +150		°C
Typical thermal resistance per leg	TO-220AB		RθJC	2		°C/W
	ITO-220AB			4		°C/W
Instantaneous forward voltage per diode			VF(1)	TYP.	MAX.	V
	IF=3A	TJ=25°C		0.74	0.78	
	IF=3A	TJ=125°C		0.68	-	
	IF=10A	TJ=25°C		0.85	-	
	IF=10A	TJ=125°C		0.80	-	
Instantaneous reverse current per diode at rated reverse voltage		TJ=25°C	IR(2)	1	5	uA
		TJ=125°C		-	80	uA

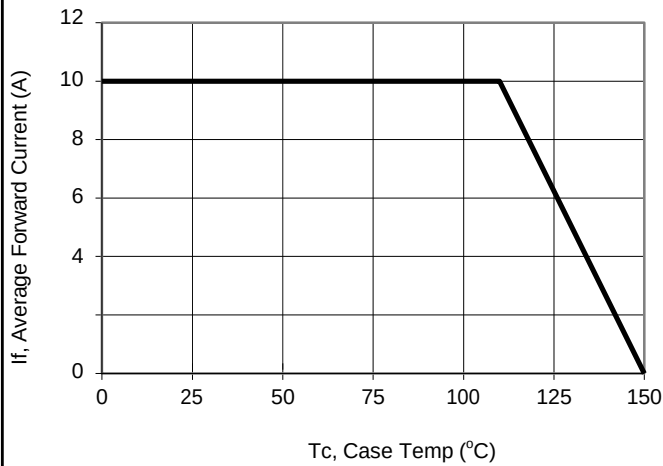
Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

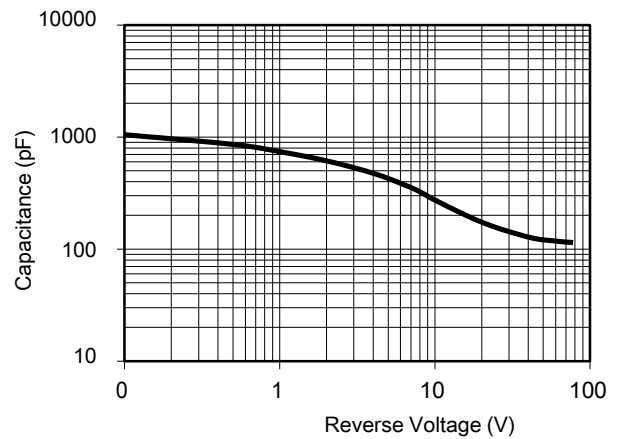
(2) Pulse test: Pulse width ≤ 40 ms

TSR20L200CT\CTF \ Rev 1.0

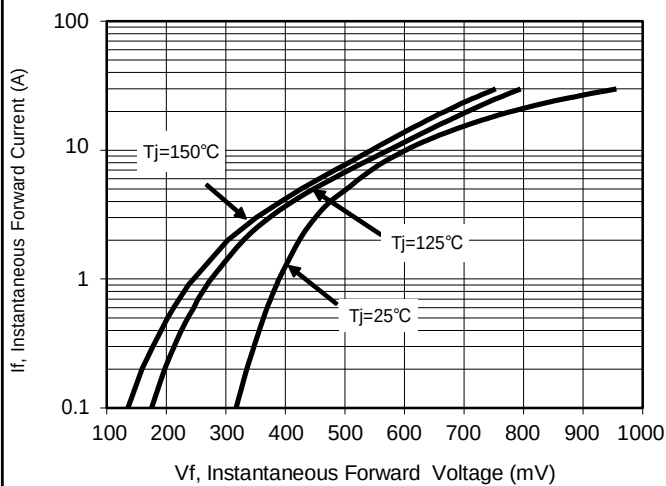
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



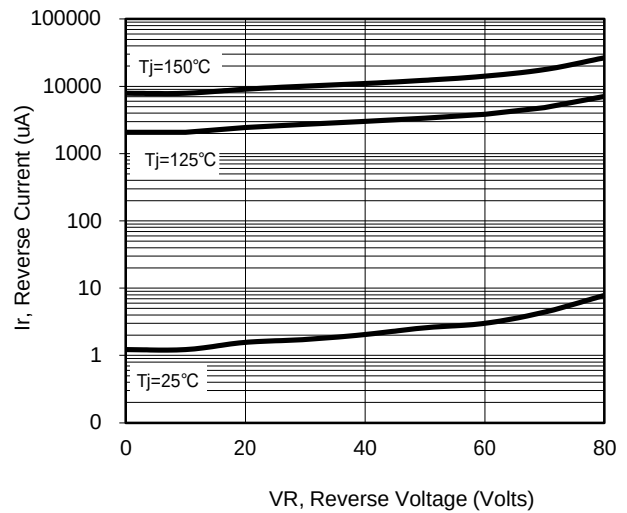
Current Derating, Case



Typical Junction Capacitance



Typical Forward Voltage



Typical Reverse Current

PACKAGE OUTLINE DIMENSIONS

